NSN 5961-01-062-3483

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View Online at https://aerobasegroup.com/nsn/5961-01-062-3483 **Inclosure Material:** Metal **Overall Length:** 0.280 inches **Overall Diameter:** Between 0.350 inches and 0.380 inches **Function For Which Designed: Amplifier Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Mounting hardware **Thread Size:** 0.164 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: -36.0 breakdown voltage, collector-to-base, emitter open and -18.0 breakdown voltage, collector-to-emitter, base open and -4.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 5.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Power output 2.8 watts; junction pattern arrangement: npn **Test Data Document:** 08771-19a134060 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unc **Terminal Type And Quantity:** 4 ribbon Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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